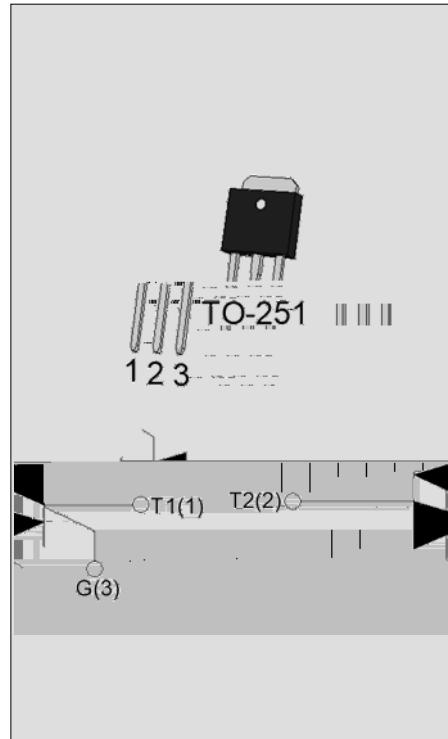




DESCRIPTION:

The ACJT810-10H triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJT810-10H embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. Package TO-251 is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	1000	V
$I_{GT} / /$	10/10/10	mA

ABSOLUTE MAXIMUM RATINGS

Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	1000	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	1000	V
RMS on-state current ($T_c = 93^\circ C$)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle , $t_p=20ms$, $T_j=25^\circ C$)	I_{TSM}	80	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$, $T_j=25^\circ C$)		88	
I^2t value for fusing ($t_p=10ms$, $T_j=25^\circ C$)	I^2t	32	A^2s
Critical rate of rise of on-state current ($I_G=2mA$ I_{GT} , $f=100Hz$, $T_j=125^\circ C$)	dI/dt	100	$A/\mu s$
Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W



Peak pulse voltage (T _j =25 ; non-repetitive,off-state;FIG.7)	V _{pp}	2	kV
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ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

I _{GT}	V _D =12V R _L =33	- -	MAX.	10	mA
V _{GT}		- -	MAX.	1	V
V _{GD}	V _D =V _{DRM} T _j =125 R _L =3.3K	- -	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	-	MAX.	25	mA
				30	
I _H	I _T =100mA		MAX.	15	mA
dV/dt	V _D =670V Gate Open T _j =125		MIN.	300	V/μs
(dI/dt)c	(dV/dt)c=10V/μs, T _j =125		MIN.	3	A/ms
t _{on}	I _G =20mA I _A =200mA I _R =20mA T _j =25	TYP.	4	μs	
t _{off}			50		
V _{CL}	I _{CL} =0.1mA t _p =1ms		MIN.	1050	V

STATIC CHARACTERISTICS

V _{TM}	I _{TM} =10A t _p =380μs	T _j =25	1.4	V
V _{TO}	Threshold voltage	T _j =125	0.78	V
R _D	Dynamic resistance	T _j =125	38	m
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25	8	μA
I _{RRM}		T _j =125	0.8	mA

THERMAL RESISTANCES

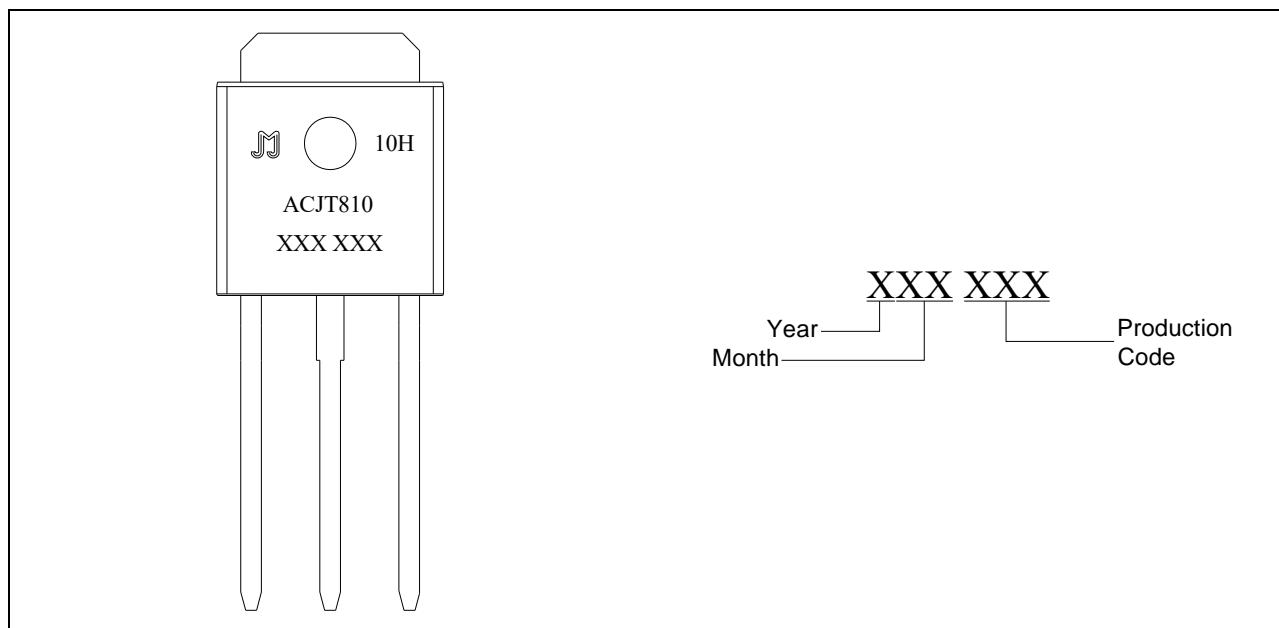
R _{th(j-c)}	junction to case (AC)	3	/W
R _{th(j-a)}	junction to ambient (AC)	100	/W



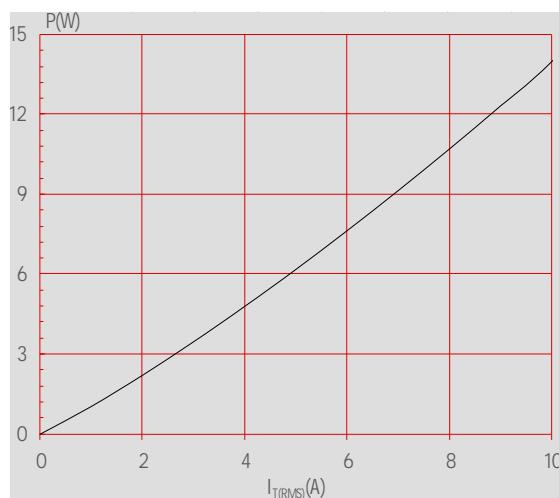
ORDERING INFORMATION

AC	J	T	8	10	-10	H
<u>AC switch</u>						
<u>JieJie Microelectronics Co.,Ltd.</u>		<u>Triacs</u>				
			<u>$I_{T(RMS)}:8A$</u>			
				<u>10: I_{GT1-3} 10mA</u>	<u>10: V_{DRM} / V_{RRM} 1000V</u>	
						<u>H:TO-251</u>

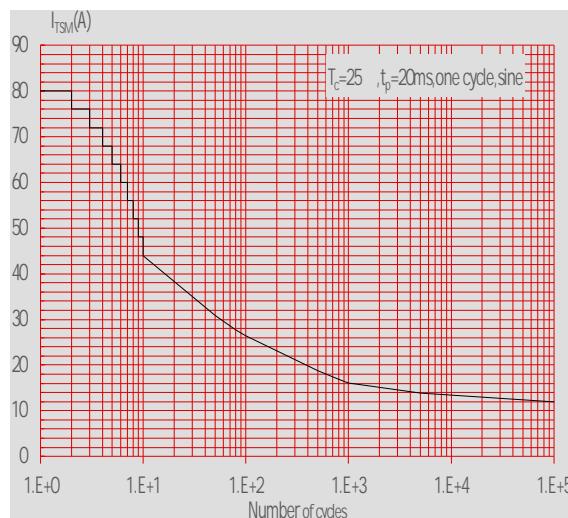
MARKING



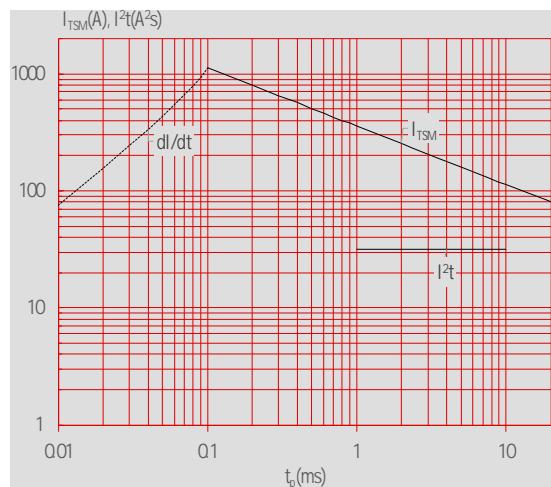
Maximum power dissipation versus RMS on-state current



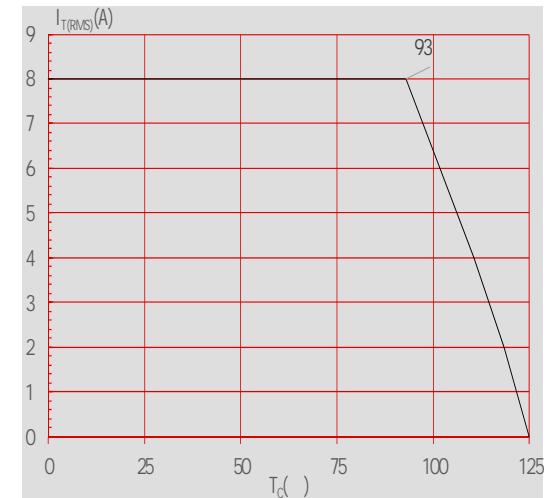
Surge peak on-state current versus number of cycles



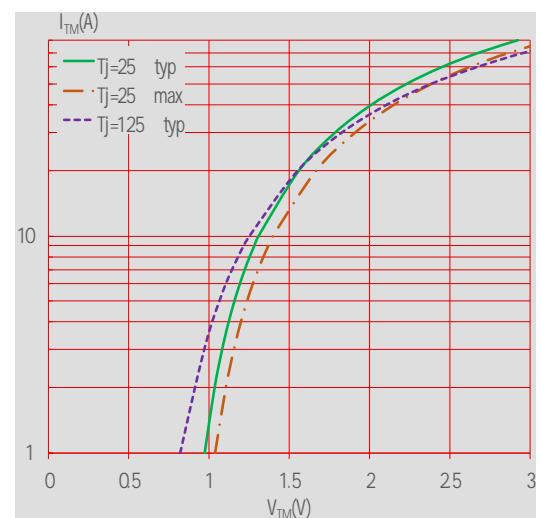
Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($dl/dt < 100\text{A}/\mu\text{s}$)



RMS on-state current versus case temperature



On-state characteristics



Relative variations of gate trigger current, holding current and latching current versus junction temperature

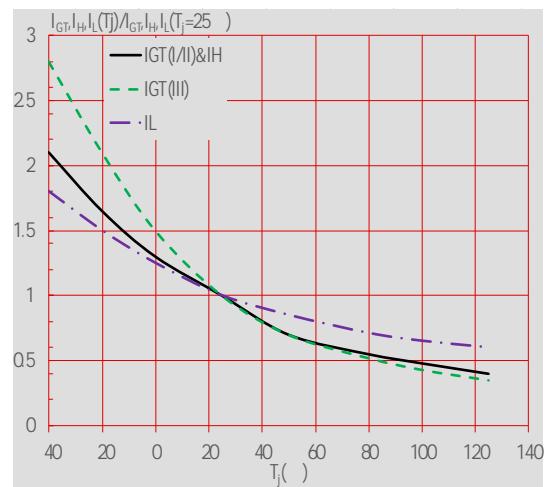
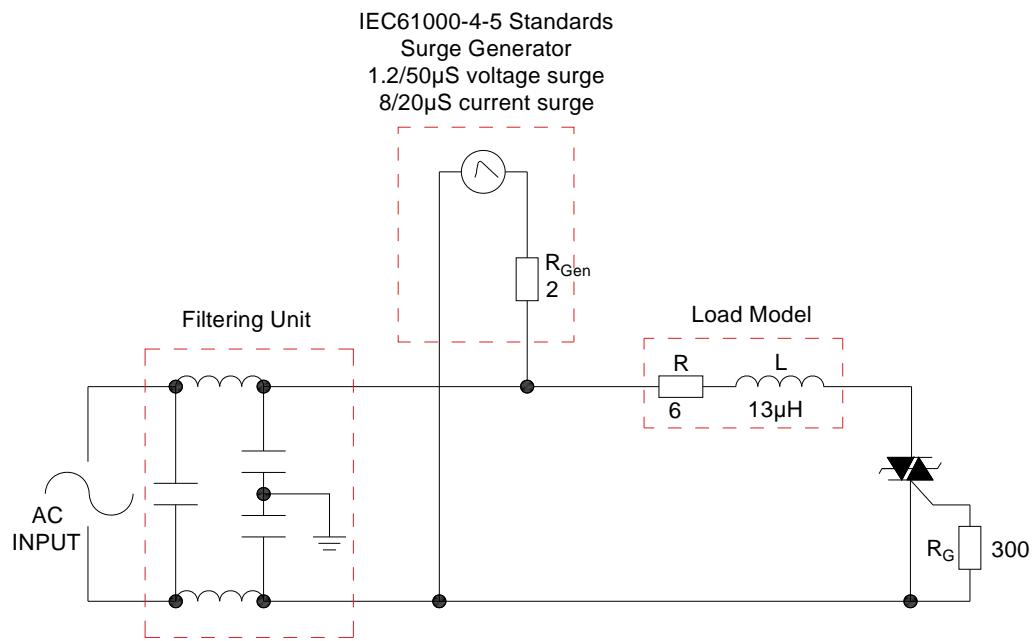




FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie

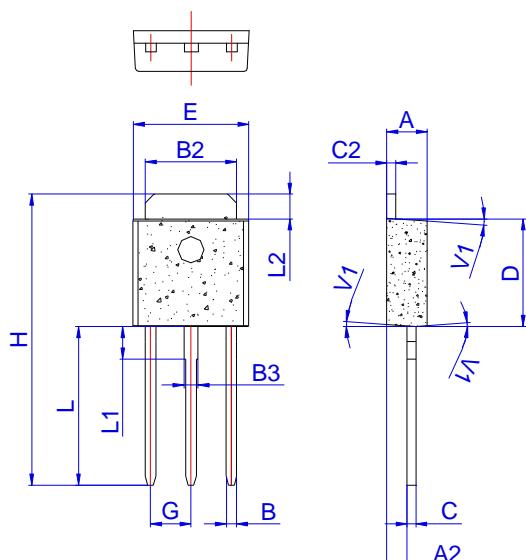


ORDERING INFORMATION

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last updated

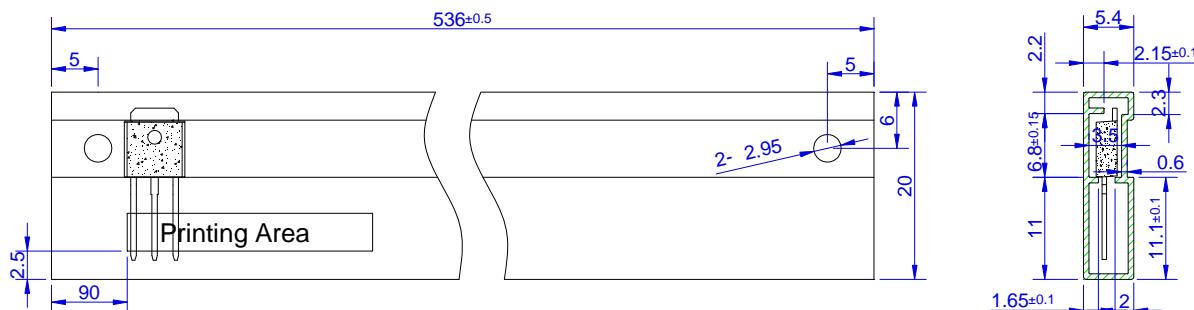


PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	1.00		1.30	0.039		0.051
B	0.50		0.70	0.020		0.028
B2	5.10		5.40	0.200		0.213
B3	0.70		1.00	0.028		0.039
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	2.20		2.40	0.087		0.094
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		2.20	0.071		0.087
L2	1.25		1.55	0.049		0.061
V1				4°		4°

DELIVERY MODE



TO-251	TUBE	80	4,000	20,000
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